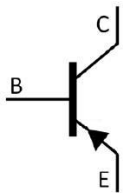


Rev.F Apr.-2017

Silicon PNP transistor in a SOT-23 Plastic Package.

High voltage, low saturation voltage, low collector output capacitance, complementary pair with MMBTA42.

High voltage control circuit.



PIN1 Base PIN 2 Emitter PIN 3 Collector

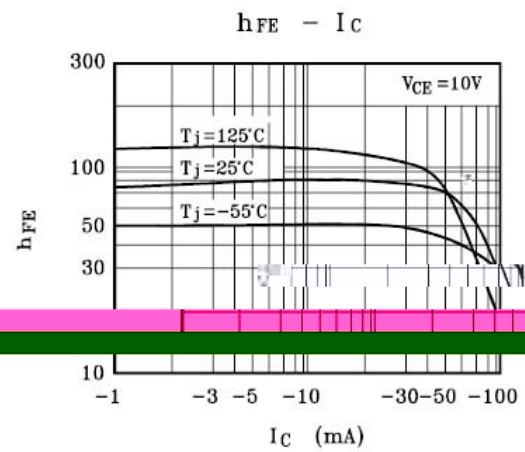
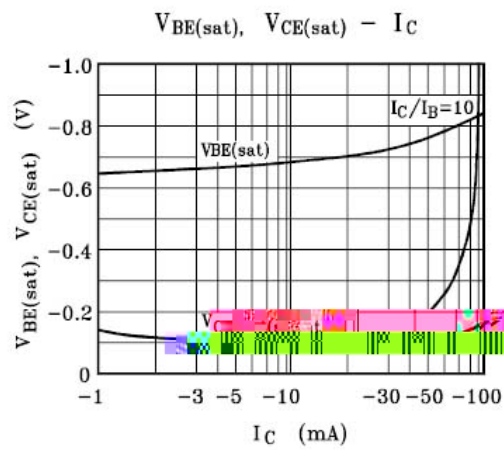
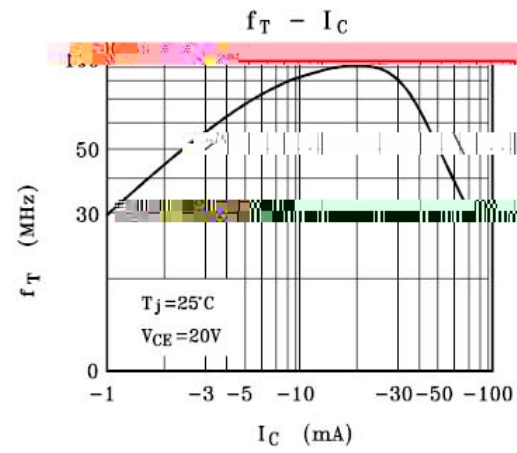
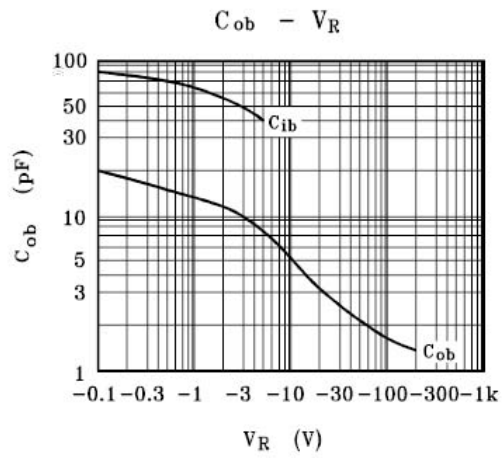
h_{FE} Range	>40
Marking	H2D

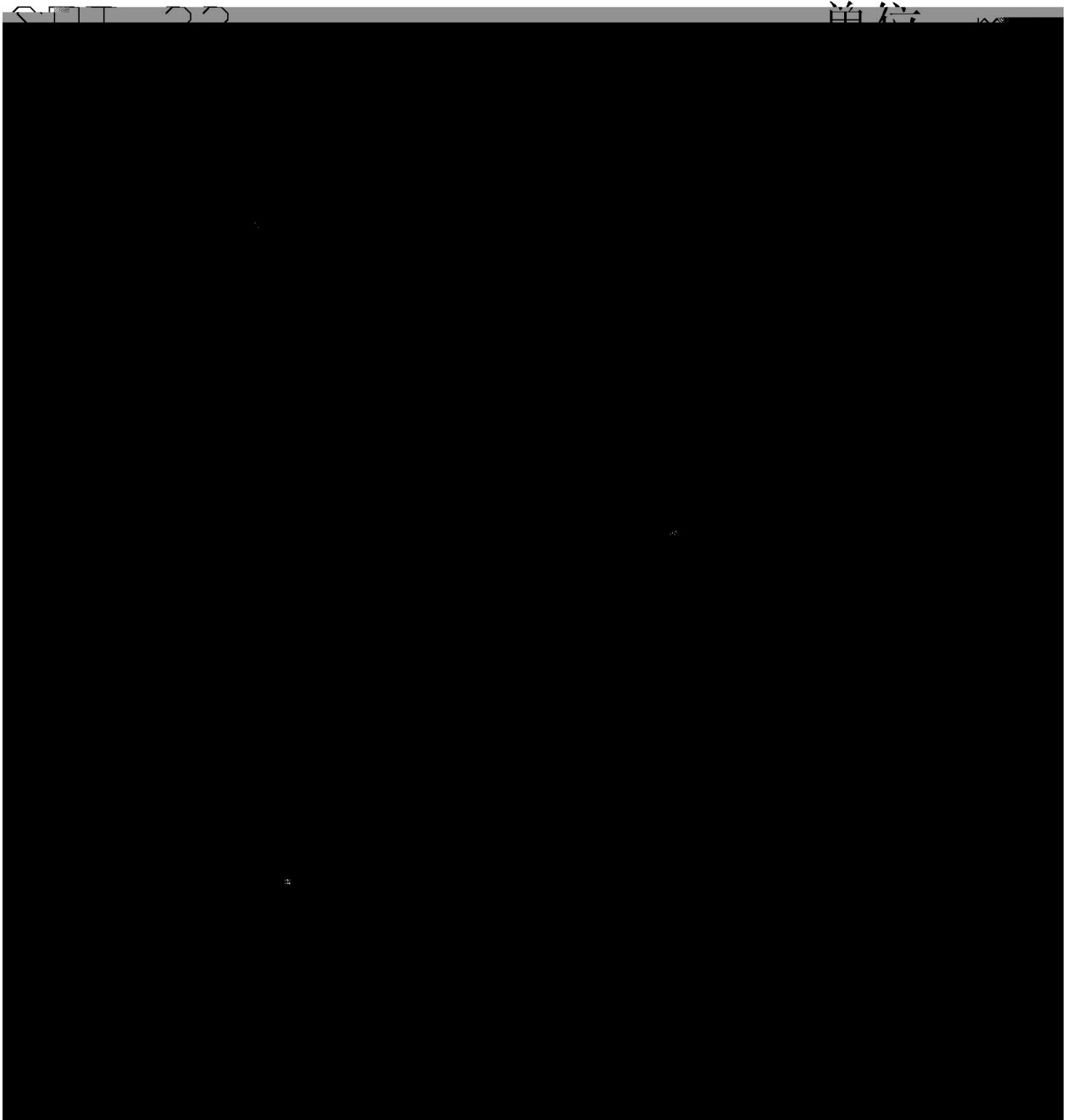
Rev.F Apr.-2017

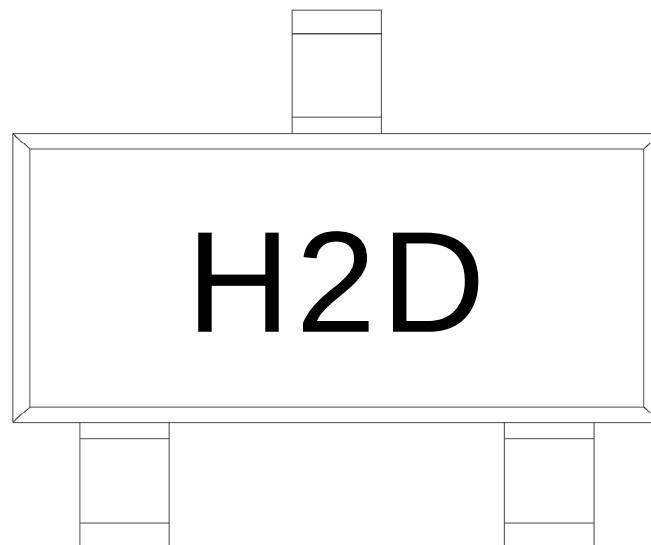
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-300	V
Collector to Emitter Voltage	V_{CEO}	-300	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A$ $I_E = 0$	-300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-300			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -100\mu A$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -200V$ $I_E = 0$				

Rev.F Apr.-2017







H

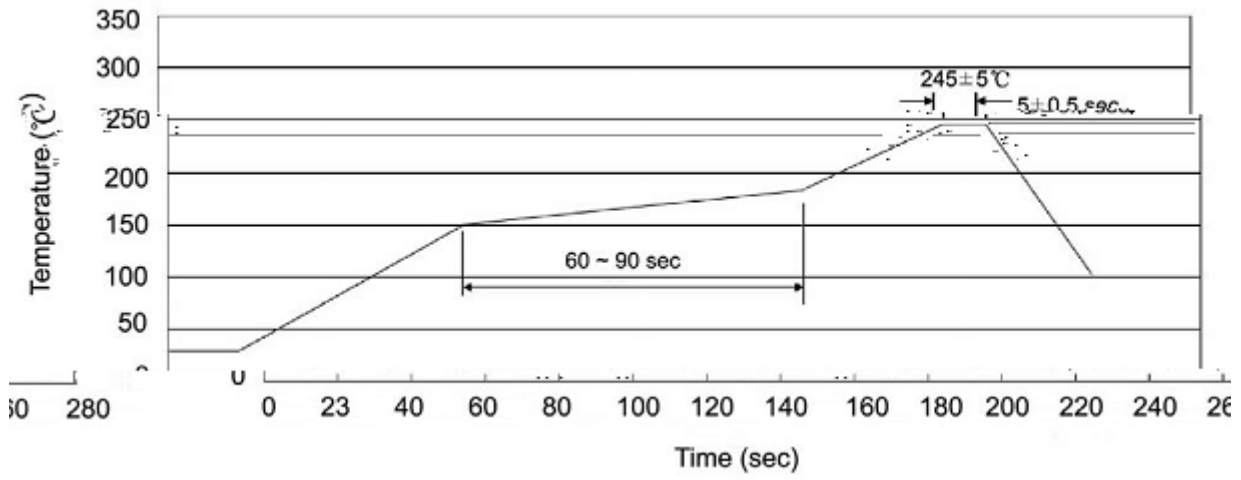
2D

Note:

H: Company Code.

2D: Product Type Code.

Rev.F Apr.-2017



Note:

1